Dual Buffer

The NL27WZ16 is a high performance dual buffer operating from a 1.65 to 5.5 V supply. At $V_{CC}=3$ V, high impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance.

Features

- Extremely High Speed: t_{PD} 2.0 ns (typical) at $V_{CC} = 5 \text{ V}$
- Designed for 1.65 V to 5.5 V V_{CC} Operation
- Over Voltage Tolerant Inputs
- \bullet LVTTL Compatible Interface Capability With 5 V TTL Logic with V_{CC} = 3 V
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- Chip Complexity: FET = 72; Equivalent Gate = 18
- Pb-Free Packages are Available

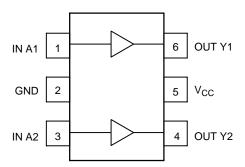


Figure 1. Pinout (Top View)

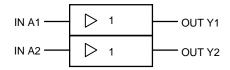


Figure 2. Logic Symbol



ON Semiconductor®

http://onsemi.com





SC-88/SC-70-6/SOT-363 DF SUFFIX CASE 419B





TSOP-6 DT SUFFIX CASE 318G



MR = Device Code
M = Date Code*

- Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position and underbar may vary depending upon manufacturing location.

PIN ASSIGNMENT

1	IN A1
2	GND
3	IN A2
4	OUT Y2
5	V _{CC}
6	OUT Y1

FUNCTION TABLE

A Input	₹ Output
L	L
Н	Н

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Chara	cteristics	Symbol	Value	Unit
DC Supply Voltage		V _{CC}	-0.5 to +7.0	V
DC Input Voltage		VI	$-0.5 \le V_I \le +7.0$	V
DC Output Voltage	Output in Z or LOW State (Note 1)	Vo	$-0.5 \le V_{O} \le 7.0$	V
DC Input Diode Current	V _I < GND	I _{IK}	-50	mA
DC Output Diode Current	V _O < GND	I _{OK}	-50	mA
DC Output Sink Current		I _O	±50	mA
DC Supply Current per Supply Pin		I _{CC}	± 100	mA
DC Ground Current per Ground Pin		I _{GND}	± 100	mA
Storage Temperature Range		T _{STG}	-65 to +150	°C
Power Dissipation in Still Air	SC-88, TSOP-6	P _D	200	mW
Thermal Resistance	SC-88, TSOP-6	θ_{JA}	333	°C/W
Lead Temperature, 1 mm from Case for 10	Seconds	TL	260	°C
Junction Temperature Under Bias		TJ	+ 150	°C
ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	V _{ESD}	> 2000 > 200 N/A	V
Latchup Performance	Above V _{CC} and Below GND at 85°C (Note 5)	I _{Latchup}	± 500	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. I_O absolute maximum rating must be observed.
- Tested to EIA/JESD22-A114-A
 Tested to EIA/JESD22-A115-A
- 4. Tested to JESD22-C101-A
- 5. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit	
Supply Voltage	Operating Data Retention Only	V _{CC}	1.65 1.5	5.5 5.5	V
Input Voltage		VI	0	5.5	V
Output Voltage	(High or LOW State)	Vo	0	5.5	V
Operating Free–Air Temperature		T _A	-40	+85	°C
Input Transition Rise or Fall Rate	$V_{CC} = 1.8 \text{ V } \pm 0.15 \text{ V}$ $V_{CC} = 2.5 \text{ V } \pm 0.2 \text{ V}$ $V_{CC} = 3.0 \text{ V } \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V } \pm 0.5 \text{ V}$	Δt/ΔV	0 0 0	20 20 10 5	ns/V

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	T _A = 25°C		С	-40°C ≤	T _A ≤ 85°C	
Parameter	Condition	Symbol	(V)	Min	Тур	Max	Min	Max	Unit
High-Level Input Voltage		V _{IH}	1.65 to 1.95 2.3 to 5.5	0.75 V _{CC} 0.7 V _{CC}			0.75 V _{CC} 0.7 V _{CC}		V
Low-Level Input Voltage		V _{IL}	1.65 to 1.95 2.3 to 5.5			0.25 V _{CC} 0.3 V _{CC}		0.25 V _{CC} 0.3 V _{CC}	V
High-Level Output Voltage V _{IN} = V _{IH}	I _{OH} = -100 μA	V _{OH}	1.65 1.8 2.3 3.0 4.5	1.55 1.7 2.2 2.9 4.4	1.65 1.8 2.3 3.0 4.5		1.55 1.7 2.2 2.9 4.4		V
	$I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$ $I_{OH} = -16 \text{ mA}$ $I_{OH} = -24 \text{ mA}$ $I_{OH} = -32 \text{ mA}$		1.65 2.3 3.0 3.0 4.5	1.29 1.9 2.4 2.3 3.8	1.52 2.15 2.80 2.68 4.20		1.29 1.9 2.4 2.3 3.8		V
Low-Level Output Voltage V _{IN} = V _{IL}	I _{OL} = 100 μA	V _{OL}	1.65 1.8 2.3 3.0 4.5		0.0 0.0 0.0 0.0 0.0	0.1 0.1 0.1 0.1 0.1		0.1 0.1 0.1 0.1 0.1	V
	I _{OL} = 4 mA I _{OL} = 8 mA I _{OL} = 16 mA I _{OL} = 24 mA I _{OL} = 32 mA		1.65 2.3 3.0 3.0 4.5		0.08 0.10 0.15 0.22 0.22	0.24 0.30 0.40 0.55 0.55		0.24 0.30 0.40 0.55 0.55	V
Input Leakage Current	$0 \text{ V} \leq \text{V}_{\text{IN}} \leq 5.5 \text{ V}$	I _{IN}	0 to 5.5			±1.0		±1.0	μΑ
Power Off Leakage Current	V _{IN} or V _{OUT} = 5.5 V	I _{OFF}	0.0			1.0		10	μА
Quiescent Supply Current	V _{IN} = 5.5 V, GND	lcc	1.65 to 5.5			1.0		10	μΑ

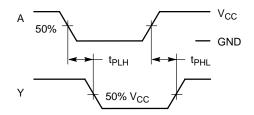
AC ELECTRICAL CHARACTERISTICS t_R = t_F = 2.5 ns; C_L = 50 pF; R_L = 500 Ω

				T _A = 25°C		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le 85^{\circ}\text{C}$					
Parameter	Condition	Symbol	V _{CC} (V)	Min	Тур	Max	Min	Max	Unit		
Propagation Delay (Figure 3 and 4)	, ,	$R_L = 1 \text{ M}\Omega$, $C_L = 15 \text{ pF}$	t _{PLH}	1.8 ± 0.15	1.8	8.0	9.6	1.8	10.2	ns	
	$R_L = 1 \text{ M}\Omega$, $C_L = 15 \text{ pF}$	3.3	2.5 ± 0.2	1.0	3.0	5.2	1.0	5.8			
	$R_L = 1 \text{ M}\Omega, C_L = 15 \text{ pF}$			ļ	3.3 ± 0.3	0.8	2.3	3.6	0.8	4.0	
	$R_L = 500 \Omega, C_L = 50 pF$		3.3 ± 0.3	1.2	3.0	4.6	1.2	5.1			
	$R_L = 1 \text{ M}\Omega$, $C_L = 15 \text{ pF}$		F0 + 0 F	0.5	1.8	2.9	0.5	3.2			
	$R_L = 500 \Omega, C_L = 50 pF$		5.0 ± 0.5	0.8	2.4	3.8	0.8	4.2			

CAPACITIVE CHARACTERISTICS

Parameter	Condition	Symbol	Typical	Unit
Input Capacitance	$V_{CC} = 5.5 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	C _{IN}	7.0	pF
Power Dissipation Capacitance (Note 6)	10 MHz, $V_{CC} = 3.3 \text{ V}$, $V_{I} = 0 \text{ V}$ or V_{CC} 10 MHz, $V_{CC} = 5.5 \text{ V}$, $V_{I} = 0 \text{ V}$ or V_{CC}	C _{PD}	9 11	pF

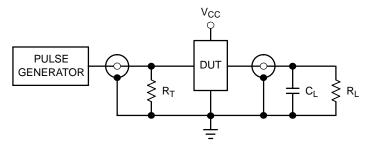
^{6.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



PROPAGATION DELAYS

 $t_R = t_F = 2.5 \text{ ns}$, 10% to 90%; f = 1 MHz; $t_W = 500 \text{ ns}$

Figure 3. Switching Waveforms



 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

ORDERING INFORMATION

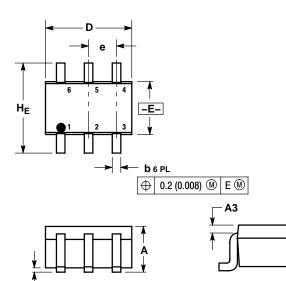
Device	Package	Shipping [†]
NL27WZ16DFT2	SC-88/SC-70/SOT-363	
NL27WZ16DFT2G	SC-88/SC-70/SOT-363 (Pb-Free)	3000 /Tape & Reel
NL27WZ16DTT1	TSOP-6	3000 / Tape & Reel
NL27WZ16DTT1G	TSOP-6 (Pb-Free)	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363

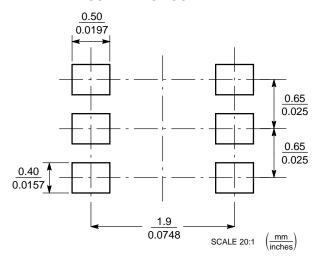
CASE 419B-02 ISSUE W



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

	MILLIMETERS				INCHES	3		
DIM	MIN	NOM	MAX	MIN	NOM	MAX		
Α	0.80	0.95	1.10	0.031	0.037	0.043		
A1	0.00	0.05	0.10	0.000	0.002	0.004		
А3		0.20 REF			0.008 REF			
b	0.10	0.21	0.30	0.004	0.008	0.012		
C	0.10	0.14	0.25	0.004	0.005	0.010		
D	1.80	2.00	2.20	0.070	0.078	0.086		
Е	1.15	1.25	1.35	0.045	0.049	0.053		
е	0.65 BSC			0	.026 BS	С		
L	0.10	0.20	0.30	0.004	0.008	0.012		
HE	2.00	2.10	2.20	0.078	0.082	0.086		

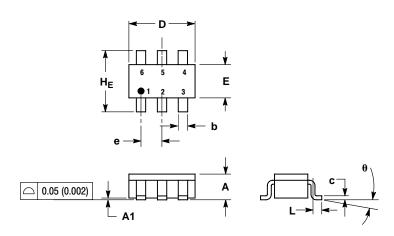
SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSOP-6 CASE 318G-02 ISSUE S

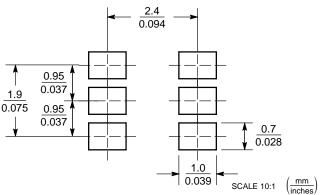


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- . CONTROLLING DIMENSION: MILLIMETER.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.38	0.50	0.010	0.014	0.020
С	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	-	10°	0°	ı	10°

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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